

SN74LXCH1T45 シングル・ビット、デュアル電源バス・トランシーバ、構成可能な電圧変換、3 ステート出力、バス・ホールド入力

1 特長

- 完全に構成可能なデュアル・レール設計により、各ポートは 1.1V~5.5V で動作可能
- 堅牢でグリッチの発生しない電源シーケンシング
- 3.3V~5.0V で最高 420Mbps をサポート
- データ入力時のバス・ホールドにより、外付けプルアップ/プルダウン抵抗が不要
- シュミット・トリガ制御入力により低速またはノイズの多い入力に対応
- スタティック・プルダウン抵抗を内蔵した制御入力により、制御入力のフローティングが可能
- 高い駆動強度 (5V で最大 32mA)
- 低い消費電力
 - 最大 3μA (25°C)
 - 最大 6μA (-40°C~125°C)
- V_{CC} 絶縁および V_{CC} 切断機能
 - どちらかの V_{CC} 電源が 100mV 未満になると、すべての I/O が高インピーダンス化
 - I_{off-float} により V_{CC} 切断動作をサポート
- I_{off} により部分的パワーダウン・モードでの動作をサポート
- LVC ファミリのレベル・シフトと互換
- 制御ロジック (DIR) は V_{CCA} 基準
- 動作温度範囲: -40°C~+125°C
- JESD 78、Class II 準拠で 100mA 超のラッチアップ性能
- JESD 22 を上回る ESD 保護
 - 人体モデル 4000V
 - デバイス帯電モデル 1000V

2 アプリケーション

- 低速またはノイズの多い入力信号の除去
- インジケータ LED または ブザーの駆動
- メカニカル・スイッチのデバウンス
- 汎用 I/O レベル・シフト

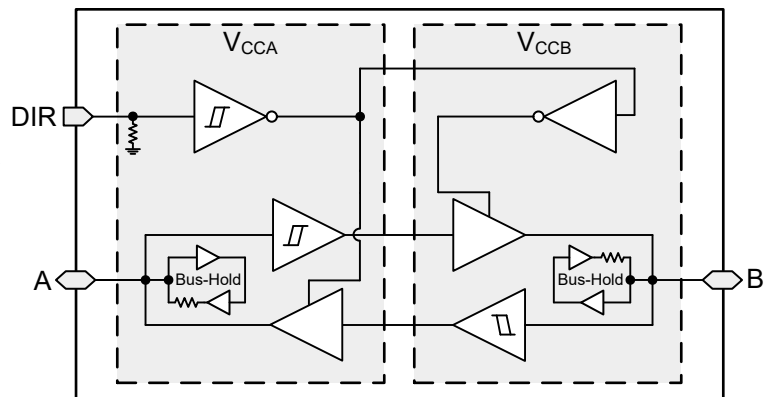
3 説明

SN74LXCH1T45 は、バス・ホールド回路を備えた 1 ビット、デュアル電源、非反転、双方向の電圧レベル変換デバイスです。I/O ピン A および制御ピン (DIR) は V_{CCA} のロジック・レベルを基準とし、I/O ピン B は V_{CCB} ロジック・レベルを基準とします。A ピンは 1.1V~5.5V の範囲の I/O 電圧を受け入れ、B ポートは 1.1V~5.5V の I/O 電圧を受け入れます。DIR が HIGH のときは A から B へ、DIR が LOW のときは B から A へデータが転送されます。制御ロジックの概要については [デバイス機能モード](#) を参照してください。

製品情報⁽¹⁾

部品番号	パッケージ	本体サイズ (公称)
SN74LXCH1T45	SC70 (DCK) (6)	2.00mm × 1.25mm
	SON (DRY) (6)	1.45mm × 1.00mm
	X2SON (DTQ) (6)	1.00mm × 0.80mm

(1) 利用可能なパッケージについては、このデータシートの末尾にある注文情報を参照してください。



Note: Bus-hold circuits are only present for data inputs, not control inputs

機能ブロック図



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4 Revision History

DATE	REVISION	NOTES
April 2022	*	Initial Release

5 Pin Configuration and Functions

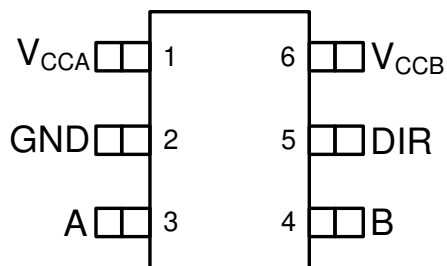


图 5-1. DCK Package, 6-Pin SC70
(Top View)

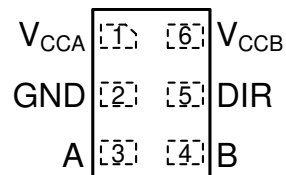


图 5-2. DRY Package Preview, 6-Pin SON
(Top View)

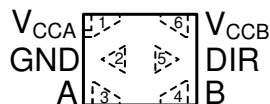


图 5-3. DTQ Package Preview, 6-Pin X2SON Transparent (Top View)

表 5-1. Pin Functions

PIN		TYPE ⁽¹⁾	DESCRIPTION
NAME	NO.		
A	3	I/O	Input or output A. Referenced to V_{CCA} .
B	4	I/O	Input or output B. Referenced to V_{CCB} .
DIR	5	I	Direction-control signal for all ports. Referenced to V_{CCA} .
GND	2	—	Ground.
DIR	5	I	Direction-control signal for all ports. Referenced to V_{CCA} .
V_{CCA}	1	—	A-port supply voltage. $1.1\text{ V} \leq V_{CCA} \leq 5.5\text{ V}$.
V_{CCB}	6	—	B-port supply voltage. $1.1\text{ V} \leq V_{CCB} \leq 5.5\text{ V}$.

(1) I = input, O = output, GND = ground

6 Specifications

6.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)⁽¹⁾

			MIN	MAX	UNIT
V_{CCA}	Supply voltage A		-0.5	6.5	V
V_{CCB}	Supply voltage B		-0.5	6.5	V
V_I	Input Voltage ⁽²⁾	I/O Ports (A Port)	-0.5	6.5	V
		I/O Ports (B Port)	-0.5	6.5	
		Control Inputs	-0.5	6.5	
V_O	Voltage applied to any output in the high-impedance or power-off state ⁽²⁾	A Port	-0.5	6.5	V
		B Port	-0.5	6.5	
V_O	Voltage applied to any output in the high or low state ^{(2) (3)}	A Port	-0.5	$V_{CCA} + 0.5$	V
		B Port	-0.5	$V_{CCB} + 0.5$	
I_{IK}	Input clamp current	$V_I < 0$	-50		mA
I_{OK}	Output clamp current	$V_O < 0$	-50		mA
I_O	Continuous output current		-50	50	mA
	Continuous current through V_{CC} or GND		-200	200	mA
T_j	Junction Temperature			150	°C
T_{stg}	Storage temperature		-65	150	°C

- (1) Stresses beyond those listed under [Absolute Maximum Ratings](#) may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under [Recommended Operating Conditions](#). Exposure beyond the limits listed in [Recommended Operating Conditions](#) may affect device reliability.
- (2) The input voltage and output negative-voltage ratings may be exceeded if the input and output current ratings are observed.
- (3) The output positive-voltage rating may be exceeded up to 6.5 V maximum if the output current rating is observed.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 ⁽¹⁾	±4000	V
		Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002 ⁽²⁾	±1000	

- (1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
- (2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted) ⁽¹⁾

				MIN	MAX	UNIT
V _{CCA}	Supply voltage A			1.1	5.5	V
V _{CCB}	Supply voltage B			1.1	5.5	V
V _{IH}	High-level input voltage	Data Inputs (A,B) (Referenced to V _{CCI})	V _{CCI} = 1.1 V - 1.3 V	V _{CCI} × 0.8	V	
			V _{CCI} = 1.4 V - 1.95 V	V _{CCI} × 0.65		
			V _{CCI} = 2.3 V - 2.7 V	1.7		
			V _{CCI} = 3.0 V - 3.6 V	2		
			V _{CCI} = 4.5 V - 5.5 V	V _{CCI} × 0.7		
V _{IL}	Low-level input voltage	Data Inputs (A,B) (Referenced to V _{CCI})	V _{CCI} = 1.1 V - 1.3 V	V _{CCI} × 0.2	V	
			V _{CCI} = 1.4 V - 1.95 V	V _{CCI} × 0.35		
			V _{CCI} = 2.3 V - 2.7 V	0.7		
			V _{CCI} = 3.0 V - 3.6 V	0.8		
			V _{CCI} = 4.5 V - 5.5 V	V _{CCI} × 0.3		
I _{OH}	High-level output current		V _{CCO} = 1.1 V	−0.1	mA	
			V _{CCO} = 1.4 V	−4		
			V _{CCO} = 1.65 V	−8		
			V _{CCO} = 2.3 V	−12		
			V _{CCO} = 3 V	−24		
			V _{CCO} = 4.5 V	−32		
I _{OL}	Low-level output current		V _{CCO} = 1.1 V	0.1	mA	
			V _{CCO} = 1.4 V	4		
			V _{CCO} = 1.65 V	8		
			V _{CCO} = 2.3 V	12		
			V _{CCO} = 3 V	24		
			V _{CCO} = 4.5 V	32		
V _I	Input voltage			0	5.5	V
V _O	Output voltage	Active State	0	V _{CCO}	V	
		Tri-State	0	5.5		
T _A	Operating free-air temperature			−40	125	°C

(1) V_{CCI} is the V_{CC} associated with the input port. V_{CCO} is the V_{CC} associated with the output port.

6.4 Thermal Information

THERMAL METRIC ⁽¹⁾		SN74LXCH1T45			UNIT
		DCK (SC70)	DRY (SON)	DTQ (X2SON)	
		6 PINS	6 PINS	6 PINS	
R _{θJA}	Junction-to-ambient thermal resistance	205.2	293.4	285.0	°C/W
R _{θJC(top)}	Junction-to-case (top) thermal resistance	132.4	184.0	140.0	°C/W
R _{θJB}	Junction-to-board thermal resistance	65.1	164.9	208.5	°C/W
Y _{JT}	Junction-to-top characterization parameter	48.0	28.3	6.1	°C/W
Y _{JB}	Junction-to-board characterization parameter	64.9	164.0	207.8	°C/W
R _{θJC(bottom)}	Junction-to-case (bottom) thermal resistance	N/A	N/A	N/A	°C/W

(1) For more information about traditional and new thermal metrics, see the [Semiconductor and IC Package Thermal Metrics](#) app report.

6.5 Electrical Characteristics

over operating free-air temperature range (unless otherwise noted)^{(1) (2)}

PARAMETER		TEST CONDITIONS	V _{CCA}	V _{CCB}	Operating free-air temperature (T _A)									UNIT
					25°C			–40°C to 85°C			–40°C to 125°C			
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
V _{T+}	Positive-going input-threshold voltage	Control Inputs (DIR) (Referenced to V _{CCI})	1.1 V	1.1 V				0.44	0.88	0.44	0.88	V		
			1.4 V	1.4 V				0.60	0.98	0.60	0.98			
			1.65 V	1.65 V				0.76	1.13	0.76	1.13			
			2.3 V	2.3 V				1.08	1.56	1.08	1.56			
			3 V	3 V				1.48	1.92	1.48	1.92			
			4.5 V	4.5 V				2.19	2.74	2.19	2.74			
			5.5 V	5.5 V				2.65	3.33	2.65	3.33			
V _{T-}	Negative-going input-threshold voltage	Control Inputs (DIR) (Referenced to V _{CCI})	1.1 V	1.1 V				0.17	0.48	0.17	0.48	V		
			1.4 V	1.4 V				0.28	0.59	0.28	0.59			
			1.65 V	1.65 V				0.35	0.69	0.35	0.69			
			2.3 V	2.3 V				0.56	0.97	0.56	0.97			
			3 V	3 V				0.89	1.5	0.89	1.5			
			4.5 V	4.5 V				1.51	1.97	1.51	1.97			
			5.5 V	5.5 V				1.88	2.4	1.88	2.4			
ΔV _T	Input-threshold hysteresis (V _{T+} – V _{T-})	Control Input (DIR) (Referenced to V _{CCA})	1.1 V	1.1 V				0.2	0.4	0.2	0.4	V		
			1.4 V	1.4 V				0.25	0.5	0.25	0.5			
			1.65 V	1.65 V				0.3	0.55	0.3	0.55			
			2.3 V	2.3 V				0.38	0.65	0.38	0.65			
			3 V	3 V				0.46	0.72	0.46	0.72			
			4.5 V	4.5 V				0.58	0.93	0.58	0.93			
			5.5 V	5.5 V				0.69	1.06	0.69	1.06			
V _{OH}	High-level output voltage ⁽³⁾	I _{OH} = –100 μA	1.1V – 5.5V	1.1V – 5.5V			V _{CCO} – 0.1		V _{CCO} – 0.1		V			
		I _{OH} = –4 mA	1.4 V	1.4 V			1		1					
		I _{OH} = –8 mA	1.65 V	1.65 V			1.2		1.2					
		I _{OH} = –12 mA	2.3 V	2.3 V			1.9		1.9					
		I _{OH} = –24 mA	3 V	3 V			2.4		2.4					
		I _{OH} = –32 mA	4.5 V	4.5 V			3.8		3.8					
V _{OL}	Low-level output voltage ⁽⁴⁾	I _{OL} = 100 μA	1.1V – 5.5V	1.1V – 5.5V				0.1		0.1	V			
		I _{OL} = 4 mA	1.4 V	1.4 V				0.3		0.3				
		I _{OL} = 8 mA	1.65 V	1.65 V				0.45		0.45				
		I _{OL} = 12 mA	2.3 V	2.3 V				0.3		0.3				
		I _{OL} = 24 mA	3 V	3 V				0.55		0.55				
		I _{OL} = 32 mA	4.5 V	4.5 V				0.55		0.55				
I _{BHL}	Bus-hold low sustaining current Port A or Port B ⁽⁶⁾	V _I = 0.39	1.1 V	1.1 V				4		4	μA			
		V _I = 0.49	1.4 V	1.4 V				15		10				
		V _I = 0.58	1.65 V	1.65 V				25		20				
		V _I = 0.70	2.3 V	2.3 V				45		45				
		V _I = 0.80	3 V	3 V				75		75				
		V _I = 1.35	4.5 V	4.5 V				100		100				

over operating free-air temperature range (unless otherwise noted)^{(1) (2)}

PARAMETER		TEST CONDITIONS	V _{CCA}	V _{CCB}	Operating free-air temperature (T _A)									UNIT
					25°C			–40°C to 85°C			–40°C to 125°C			
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
I _{BHH}	Bus-hold high sustaining current Port A or Port B ⁽⁷⁾	V _I = 0.71 V	1.1 V	1.1 V				–4			–4			μA
		V _I = 0.91 V	1.4 V	1.4 V				–15			–15			
		V _I = 1.07 V	1.65 V	1.65 V				–25			–25			
		V _I = 1.70 V	2.3 V	2.3 V				–45			–45			
		V _I = 2.00 V	3 V	3 V				–75			–75			
		V _I = 3.15 V	4.5 V	4.5 V				–100			–100			
I _{BHLO}	Bus-hold low overdrive current ⁽⁸⁾	Ramp input up V _I = 0 to V _{CCI}	1.3 V	1.3 V				75			75			μA
			1.6 V	1.6 V				125			125			
			1.95 V	1.95 V				200			200			
			2.7 V	2.7 V				300			300			
			3.6 V	3.6 V				500			500			
			5.5 V	5.5 V				900			900			
I _{BHHO}	Bus-hold high overdrive current ⁽⁹⁾	Ramp input down V _I = V _{CCI} to 0	1.3 V	1.3 V				–75			–75			μA
			1.6 V	1.6 V				–125			–125			
			1.95 V	1.95 V				–200			–200			
			2.7 V	2.7 V				–300			–300			
			3.6 V	3.6 V				–500			–500			
			5.5 V	5.5 V				–900			–900			
I _I	Input leakage current	Control input (DIR) V _I = V _{CCA} or GND	1.1V – 5.5V	1.1V – 5.5V	–0.1	1		–0.1	2		–0.1	2		μA
		Data Inputs ⁽⁵⁾ (A _x , B _x) V _I = V _{CCI} or GND	1.1V – 5.5V	1.1V – 5.5V	–0.3	1		–1	1		–2	2		μA
I _{off}	Partial power down current	A Port or B Port V _I or V _O = 0 V - 5.5 V	0 V	0 V - 5.5 V	–1	1		–2	2		–2.5	2.5		μA
			0 V - 5.5 V	0 V	–1	1		–2	2		–2.5	2.5		
I _{off-float}	Floating supply Partial power down current	A Port or B Port V _I or V _O = GND	Floating ⁽¹⁰⁾	0 V - 5.5 V	–1.5	1.5		–2	2		–2.5	2.5		μA
			0 V - 5.5 V	Floating ⁽¹⁰⁾	–1.5	1.5		–2	2		–2.5	2.5		
I _{CCA}	V _{CCA} supply current	V _I = V _{CCI} or GND I _O = 0	1.1V – 5.5V	1.1V – 5.5V	2			2			4			μA
			0 V	5.5 V	–0.2			–0.5			–1			
			5.5 V	0 V	1			1			2			
		V _I = GND I _O = 0	5.5 V	Floating ⁽¹⁰⁾	1.5			1.5			2			
I _{CCB}	V _{CCB} supply current	V _I = V _{CCI} or GND I _O = 0	1.1V – 5.5V	1.1V – 5.5V	2			2			4			μA
			0 V	5.5 V	1			1			2			
			5.5 V	0 V	–0.2			–0.5			–1			
		V _I = GND I _O = 0	Floating ⁽¹⁰⁾	5.5 V	1.5			1.5			2			
I _{CCA} + I _{CCB}	Combined supply current	V _I = V _{CCI} or GND I _O = 0	1.1V – 5.5V	1.1V – 5.5V	3			4			6			μA

over operating free-air temperature range (unless otherwise noted)^{(1) (2)}

PARAMETER		TEST CONDITIONS	V _{CCA}	V _{CCB}	Operating free-air temperature (T _A)									UNIT
					25°C			−40°C to 85°C			−40°C to 125°C			
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
ΔI _{CCA}	V _{CCA} additional supply current per input	Control input (DIR): V _I = V _{CCA} − 0.6 V A port = V _{CCA} or GND B Port = open	3.0V - 5.5V	3.0V - 5.5V						50			75	μA
		A Port: V _I = V _{CCA} − 0.6 V DIR = V _{CCA} , B Port = open	3.0V - 5.5V	3.0V - 5.5V						50			75	
ΔI _{CCB}	V _{CCB} additional supply current per input	B Port: V _I = V _{CCB} - 0.6 V DIR = GND, A Port = open	3.0V - 5.5V	3.0V - 5.5V						50			75	μA
C _i	Control Input Capacitance	V _I = 3.3 V or GND	3.3 V	3.3 V		2.2				4			4	pF
C _{io}	Data I/O Capacitance	V _{CCO} = 0V V _O = 1.65V DC +1 MHz -16 dBm sine wave	3.3 V	3.3 V		4.9				10			7	pF

- (1) V_{CCI} is the V_{CC} associated with the input port
- (2) V_{CCO} is the V_{CC} associated with the output port
- (3) Tested at $V_I = V_{T+(MAX)}$
- (4) Tested at $V_I = V_{T-(MIN)}$
- (5) For I/O ports, the parameter I_I includes the I_{OZ} current
- (6) I_{BHL} should be measured after lowering V_I to GND and then raising it to the defined input voltage
- (7) I_{BHH} should be measured after raising V_I to V_{CCI} and then lowering it to the defined input voltage
- (8) An external driver must source at least I_{BHL0} to switch this node from low-to-high
- (9) An external driver must sink at least I_{BHH0} to switch this node from high to low
- (10) Floating is defined as a node that is both not actively driven by an external device and has leakage not exceeding 10nA

6.6 Switching Characteristics, $V_{CCA} = 1.2 \pm 0.1 \text{ V}$

See [Figure 7-1](#) and [Table 7-1](#) for test circuit and loading. See [Figure 7-2](#), [Figure 7-3](#), and [Figure 7-4](#) for measurement waveforms.

PARAMETER		FROM	TO	Test Conditions	B-Port Supply Voltage (V _{CCB})												UNIT						
					1.2 ± 0.1 V			1.5 ± 0.1 V			1.8 ± 0.15 V			2.5 ± 0.2 V				3.3 ± 0.3 V			5.0 ± 0.5 V		
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX		MIN	TYP	MAX	MIN	TYP	MAX
t _{pd}	Propagation delay	A	B	-40°C to 85°C	6		85	4		41	3		36	1		33	1		34	1		44	ns
				-40°C to 125°C	8		55	6		37	5		33	3		30	3		30	2		33	
		B	A	-40°C to 85°C	6		85	5		71	4		67	3		60	3		57	3		58	
				-40°C to 125°C	8		55	6		47	6		43	5		38	4		37	4		36	
t _{dis}	Disable time	DIR	A	-40°C to 85°C	5		53	5		53	5		53	5		53	5		53	4		53	ns
				-40°C to 125°C	7		47	7		47	7		47	7		47	7		47	7		47	
		DIR	B	-40°C to 85°C	10		85	7		47	6		41	5		34	5		33	4		32	
				-40°C to 125°C	14		71	11		48	10		41	8		34	8		33	6		32	
t _{en}	Enable time	DIR	A	-40°C to 85°C	21		150	17		110	16		99	13		86	13		83	12		85	ns
				-40°C to 125°C	27		121	23		89	21		80	17		68	17		65	15		63	
		DIR	B	-40°C to 85°C	16		118	14		89	13		84	12		81	11		82	11		92	
				-40°C to 125°C	19		97	18		79	17		73	16		68	15		67	14		70	

6.7 Switching Characteristics, $V_{CCA} = 1.5 \pm 0.1 \text{ V}$

See [图 7-1](#) and [表 7-1](#) for test circuit and loading. See [图 7-2](#), [图 7-3](#), and [图 7-4](#) for measurement waveforms.

PARAMETER		FROM	TO	Test Conditions	B-Port Supply Voltage (V _{CCB})																		UNIT
					1.2 ± 0.1 V			1.5 ± 0.1 V			1.8 ± 0.15 V			2.5 ± 0.2 V			3.3 ± 0.3 V			5.0 ± 0.5 V			
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	
t _{pd}	Propagation delay	A	B	-40°C to 85°C	1		70	1		29	1		24	1		20	1		19	1		19	ns
				-40°C to 125°C	1		46	1		29	1		24	1		21	1		19	1		20	
		B	A	-40°C to 85°C	1		39	1		29	1		26	1		23	1		21	1		21	
				-40°C to 125°C	1		36	1		29	1		26	1		23	1		21	1		21	
t _{dis}	Disable time	DIR	A	-40°C to 85°C	3		29	3		29	3		29	3		29	3		29	3		29	ns
				-40°C to 125°C	5		29	5		29	5		29	5		29	5		29	5		29	
		DIR	B	-40°C to 85°C	11		78	8		45	7		38	5		31	5		30	4		28	
				-40°C to 125°C	15		70	14		46	11		40	10		32	9		31	8		29	
t _{en}	Enable time	DIR	A	-40°C to 85°C	19		113	15		69	13		59	11		49	11		46	9		44	ns
				-40°C to 125°C	27		101	23		70	21		61	18		51	17		48	15		45	
		DIR	B	-40°C to 85°C	12		91	10		53	9		48	8		43	8		41	7		41	
				-40°C to 125°C	16		71	14		54	13		49	12		44	12		42	11		42	

6.8 Switching Characteristics, $V_{CCA} = 1.8 \pm 0.15 \text{ V}$

See [图 7-1](#) and [表 7-1](#) for test circuit and loading. See [图 7-2](#), [图 7-3](#), and [图 7-4](#) for measurement waveforms.

PARAMETER		FROM	TO	Test Conditions	B-Port Supply Voltage (V _{CCB})												UNIT						
					1.2 ± 0.1 V			1.5 ± 0.1 V			1.8 ± 0.15 V			2.5 ± 0.2 V				3.3 ± 0.3 V			5.0 ± 0.5 V		
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX		MIN	TYP	MAX	MIN	TYP	MAX
t _{pd}	Propagation delay	A	B	-40°C to 85°C	1		66	1		26	1		21	1		17	1		16	1		15	ns
				-40°C to 125°C	1		43	1		27	1		22	1		18	1		17	1		16	
		B	A	-40°C to 85°C	1		35	1		24	1		21	1		18	1		17	1		17	
				-40°C to 125°C	1		32	1		24	1		22	1		19	1		18	1		17	
t _{dis}	Disable time	DIR	A	-40°C to 85°C	2		22	2		22	2		23	2		23	2		22	2		22	ns
				-40°C to 125°C	4		23	4		31	4		23	4		23	4		23	4		23	
		DIR	B	-40°C to 85°C	9		73	7		40	6		34	4		27	4		25	3		23	
				-40°C to 125°C	15		64	13		42	11		36	6		28	8		27	6		25	
t _{en}	Enable time	DIR	A	-40°C to 85°C	17		103	13		59	12		50	9		40	9		38	7		35	ns
				-40°C to 125°C	23		90	21		61	19		53	16		43	12		39	12		37	
		DIR	B	-40°C to 85°C	11		80	9		44	8		39	7		34	6		33	6		32	
				-40°C to 125°C	14		61	12		45	11		40	10		36	10		34	9		35	

6.9 Switching Characteristics, $V_{CCA} = 2.5 \pm 0.2 \text{ V}$

See [图 7-1](#) and [表 7-1](#) for test circuit and loading. See [图 7-2](#), [图 7-3](#), and [图 7-4](#) for measurement waveforms.

PARAMETER		FROM	TO	Test Conditions	B-Port Supply Voltage (V _{CCB})															UNIT			
					1.2 ± 0.1 V			1.5 ± 0.1 V			1.8 ± 0.15 V			2.5 ± 0.2 V			3.3 ± 0.3 V				5.0 ± 0.5 V		
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX		MIN	TYP	MAX
t _{pd}	Propagation delay	A	B	-40°C to 85°C	1		59	1		23	1		19	1		15	1		13	1		12	ns
				-40°C to 125°C	1		38	1		23	1		19	1		15	1		14	1		13	
		B	A	-40°C to 85°C	1		32	1		20	1		17	1		15	1		14	1		13	
				-40°C to 125°C	1		29	1		21	1		18	1		15	1		14	1		14	
t _{dis}	Disable time	DIR	A	-40°C to 85°C	1		16	1		23	1		16	1		16	1		20	1		16	ns
				-40°C to 125°C	2		16	2		16	2		16	2		25	2		16	2		16	
		DIR	B	-40°C to 85°C	8		63	6		35	5		29	3		23	3		22	2		19	
				-40°C to 125°C	13		56	10		37	10		31	8		25	7		23	5		20	
t _{en}	Enable time	DIR	A	-40°C to 85°C	14		91	11		49	10		41	8		33	7		30	6		27	ns
				-40°C to 125°C	21		76	18		51	16		44	14		35	13		32	10		29	
		DIR	B	-40°C to 85°C	8		67	6		33	5		33	4		25	4		24	4		23	
				-40°C to 125°C	11		49	9		34	8		30	7		27	7		27	6		24	

6.10 Switching Characteristics, $V_{CCA} = 3.3 \pm 0.3 \text{ V}$

See [图 7-1](#) and [表 7-1](#) for test circuit and loading. See [图 7-2](#), [图 7-3](#), and [图 7-4](#) for measurement waveforms.

PARAMETER		FROM	TO	Test Conditions	B-Port Supply Voltage (V _{CCB})															UNIT			
					1.2 ± 0.1 V			1.5 ± 0.1 V			1.8 ± 0.15 V			2.5 ± 0.2 V			3.3 ± 0.3 V				5.0 ± 0.5 V		
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX		MIN	TYP	MAX
t _{pd}	Propagation delay	A	B	-40°C to 85°C	1		57	1		21	1		17	1		14	1		12	1		11	ns
				-40°C to 125°C	1		36	1		22	1		18	1		14	1		13	1		12	
		B	A	-40°C to 85°C	1		33	1		19	1		16	1		13	1		12	1		12	
				-40°C to 125°C	1		29	1		19	1		17	1		14	1		13	1		12	
t _{dis}	Disable time	DIR	A	-40°C to 85°C	1		14	1		14	1		14	1		14	1		20	1		14	ns
				-40°C to 125°C	1		34	1		15	1		15	1		15	1		15	1		17	
		DIR	B	-40°C to 85°C	7		59	5		32	5		27	3		21	3		20	2		18	
				-40°C to 125°C	12		52	9		33	9		29	7		23	7		22	5		19	
t _{en}	Enable time	DIR	A	-40°C to 85°C	13		86	10		44	9		37	7		30	7		28	5		25	ns
				-40°C to 125°C	19		71	16		46	14		39	12		32	12		29	10		26	
		DIR	B	-40°C to 85°C	8		64	6		30	5		27	4		23	4		22	3		22	
				-40°C to 125°C	10		46	9		31	8		28	7		24	6		23	6		22	

6.11 Switching Characteristics, $V_{CCA} = 5.0 \pm 0.5 \text{ V}$

See [图 7-1](#) and [表 7-1](#) for test circuit and loading. See [图 7-2](#), [图 7-3](#), and [图 7-4](#) for measurement waveforms.

PARAMETER		FROM	TO	Test Conditions	B-Port Supply Voltage (V _{CCB})															UNIT			
					1.2 ± 0.1 V			1.5 ± 0.1 V			1.8 ± 0.15 V			2.5 ± 0.2 V			3.3 ± 0.3 V				5.0 ± 0.5 V		
					MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX	MIN	TYP	MAX		MIN	TYP	MAX
t _{pd}	Propagation delay	A	B	-40°C to 85°C	1		57	1		21	1		17	1		13	1		12	1		11	ns
				-40°C to 125°C	1		36	1		21	1		17	1		14	1		12	1		11	
		B	A	-40°C to 85°C	1		47	1		19	1		15	1		12	1		11	1		11	
				-40°C to 125°C	1		33	1		20	1		16	1		13	1		12	1		11	
t _{dis}	Disable time	DIR	A	-40°C to 85°C	1		12	1		12	1		21	1		12	1		15	1		12	ns
				-40°C to 125°C	1		12	1		12	1		20	1		12	1		12	1		12	
		DIR	B	-40°C to 85°C	1		57	1		30	4		25	3		20	3		19	2		17	
				-40°C to 125°C	11		50	9		31	8		27	6		21	6		20	4		18	
t _{en}	Enable time	DIR	A	-40°C to 85°C	8		98	6		42	8		34	7		27	7		25	5		23	ns
				-40°C to 125°C	18		73	15		44	13		36	11		29	11		27	9		24	
		DIR	B	-40°C to 85°C	6		62	4		28	3		24	3		20	2		19	2		18	
				-40°C to 125°C	9		43	7		28	6		25	5		21	4		20	4		19	

6.12 Switching Characteristics: T_{sk} , T_{MAX}

over operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS		V _{CCI}	V _{CCO}	Operating free-air temperature (T _A)			UNIT
					-40°C to 125°C			
					MIN	TYP	MAX	
T _{MAX} - Maximum Data Rate	50% Duty Cycle Input One channel switching 20% of pulse > 0.7*V _{CCO} 20% of pulse < 0.3*V _{CCO}	Up Translation	3.0 V – 3.6 V	4.5 V – 5.5 V	200	420	Mbps	
			2.25 V - 2.75 V	4.5 V - 5.5 V	150	300		
			1.65 V – 1.95 V	4.5 V – 5.5 V	100	200		
			1.1 V – 1.3 V	4.5 V – 5.5 V	20	40		
			1.65 V – 1.95 V	3.0 V – 3.6 V	100	210		
			1.1 V – 1.3 V	3.0 V – 3.6 V	10	20		
		Down Translation	4.5 V – 5.5 V	3.0 V – 3.6 V	100	210		
			4.5 V – 5.5 V	2.25 V - 2.75 V	75	140		
			4.5 V – 5.5 V	1.65 V – 1.95 V	50	75		
			4.5 V – 5.5 V	1.1 V – 1.3 V	15	30		
			3.0 V – 3.6 V	1.65 V – 1.95 V	40	75		
			3.0 V – 3.6 V	1.1 V – 1.3 V	10	20		
	1.65 V – 1.95 V	1.1 V – 1.3 V	5	10				
t _{sk} – Output skew	Timing skew between any two switching outputs within the same device	Up Translation	3.0 V – 3.6 V	4.5 V – 5.5 V			1	ns
			1.65 V – 1.95 V	4.5 V – 5.5 V			2	
			1.1 V – 1.3 V	4.5 V – 5.5 V			3	
			1.65 V – 1.95 V	3.0 V – 3.6 V			2.5	
			1.1 V – 1.3 V	3.0 V – 3.6 V			3.5	
			1.1 V – 1.3 V	1.65 V – 1.95 V			4.5	
		Down Translation	4.5 V – 5.5 V	3.0 V – 3.6 V			1	
			4.5 V – 5.5 V	1.65 V – 1.95 V			2	
			4.5 V – 5.5 V	1.1 V – 1.3 V			3	
			3.0 V – 3.6 V	1.65 V – 1.95 V			3	
			3.0 V – 3.6 V	1.1 V – 1.3 V			4	
			1.65 V – 1.95 V	1.1 V – 1.3 V			5	

6.13 Operating Characteristics

$T_A = 25^\circ\text{C}$ ⁽¹⁾

PARAMETER		Test Conditions	Supply Voltage ($V_{CCB} = V_{CCA}$)						UNIT
			1.2 ± 0.1V	1.5 ± 0.1V	1.8 ± 0.15V	2.5 ± 0.2V	3.3 ± 0.3V	5.0 ± 0.5V	
			TYP	TYP	TYP	TYP	TYP	TYP	
C_{pdA} ⁽²⁾	A to B	A Port CL = 0, RL = Open f = 10 MHz $t_{rise} = t_{fall} = 1$ ns	3.5	3.7	3.9	4.2	4.5	5	pF
	B to A		20.2	20.5	20.7	21.5	22.8	24.9	
C_{pdB} ⁽²⁾	A to B	B Port CL = 0, RL = Open f = 10 MHz $t_{rise} = t_{fall} = 1$ ns	20.2	20.5	20.8	21.5	22.8	24.8	pF
	B to A		3.5	3.7	3.9	4.2	4.5	5.1	

(1) See the [CMOS Power Consumption and \$C_{pd}\$ Calculation](#) application report for more information about power dissipation capacitance.

(2) C_{pdA} and C_{pdB} are respectively A-Port and B-Port power dissipation capacitances per transceiver.

6.14 Typical Characteristics

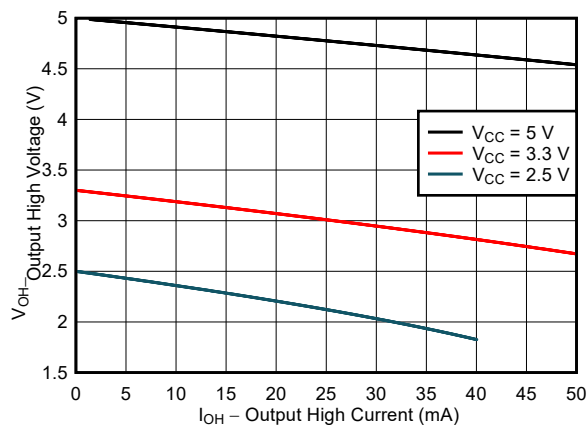


FIG 6-1. Typical ($T_A=25^\circ\text{C}$) Output High Voltage (V_{OH}) vs Source Current (I_{OH})

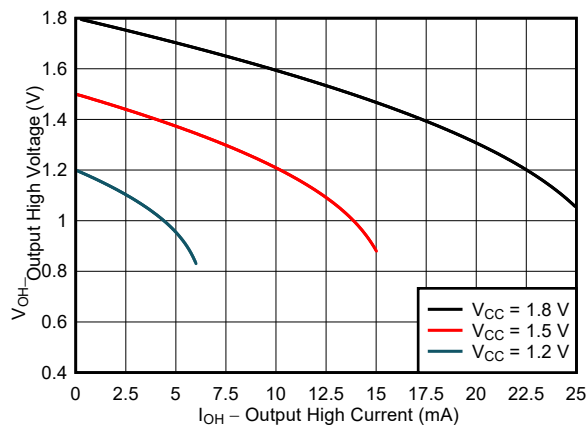


FIG 6-2. Typical ($T_A=25^\circ\text{C}$) Output High Voltage (V_{OH}) vs Source Current (I_{OH})

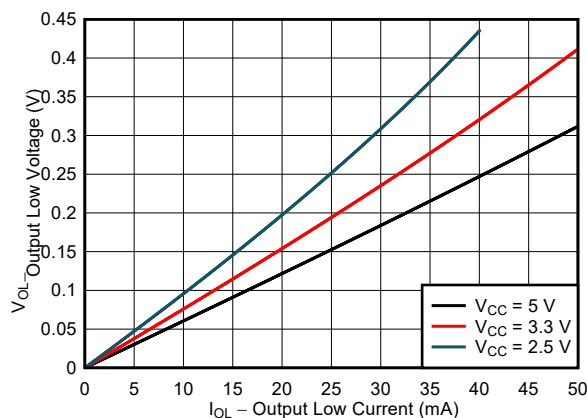


FIG 6-3. Typical ($T_A=25^\circ\text{C}$) Output Low Voltage (V_{OL}) vs Sink Current (I_{OL})

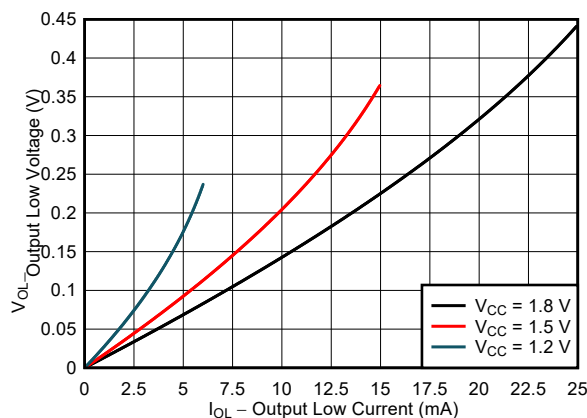


FIG 6-4. Typical ($T_A=25^\circ\text{C}$) Output Low Voltage (V_{OL}) vs Sink Current (I_{OL})

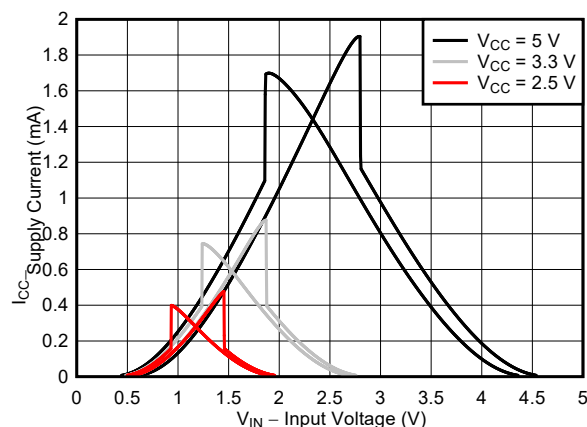


FIG 6-5. Typical ($T_A=25^\circ\text{C}$) Supply Current (I_{CC}) vs Input Voltage (V_{IN})

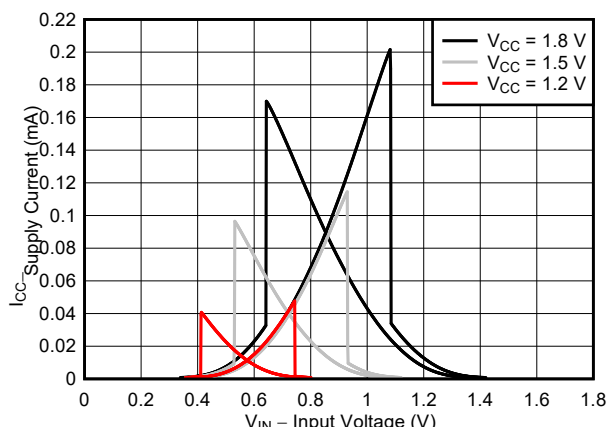


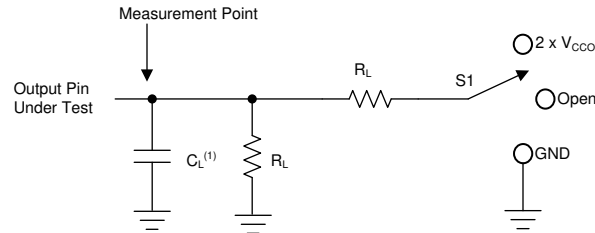
FIG 6-6. Typical ($T_A=25^\circ\text{C}$) Supply Current (I_{CC}) vs Input Voltage (V_{IN})

7 Parameter Measurement Information

7.1 Load Circuit and Voltage Waveforms

Unless otherwise noted, all input pulses are supplied by generators having the following characteristics:

- $f = 1 \text{ MHz}$
- $Z_O = 50 \Omega$
- $\Delta t / \Delta V \leq 1 \text{ ns/V}$

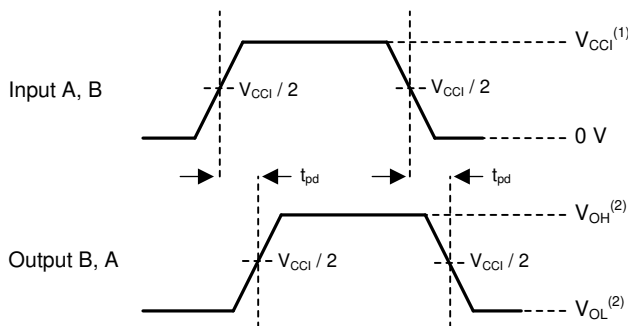


A. C_L includes probe and jig capacitance.

图 7-1. Load Circuit

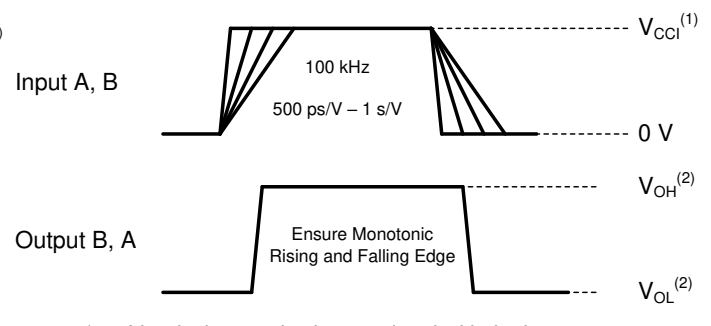
表 7-1. Load Circuit Conditions

Parameter	V_{CCO}	R_L	C_L	S_1	V_{TP}
t_{pd} Propagation (delay) time	1.1 V – 5.5 V	2 k Ω	15 pF	Open	N/A
t_{en}, t_{dis} Enable time or disable time	1.1 V – 1.6 V	2 k Ω	15 pF	$2 \times V_{CCO}$	0.1 V
	1.65 V – 2.7 V	2 k Ω	15 pF	$2 \times V_{CCO}$	0.15 V
	3.0 V – 5.5 V	2 k Ω	15 pF	$2 \times V_{CCO}$	0.3 V
t_{en}, t_{dis} Enable time or disable time	1.1 V – 1.6 V	2 k Ω	15 pF	GND	0.1 V
	1.65 V – 2.7 V	2 k Ω	15 pF	GND	0.15 V
	3.0 V – 5.5 V	2 k Ω	15 pF	GND	0.3 V



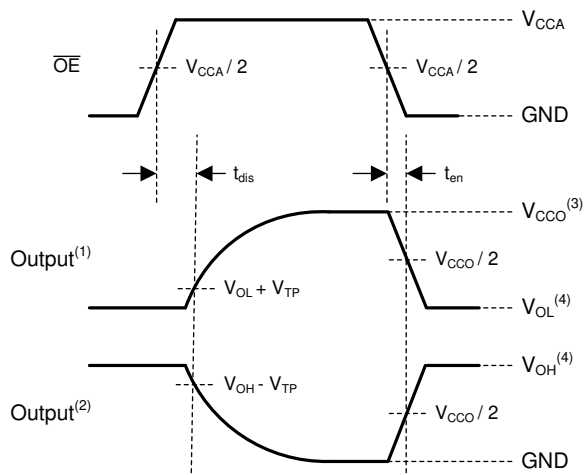
1. V_{CCI} is the supply pin associated with the input port.
2. V_{OH} and V_{OL} are typical output voltage levels that occur with specified R_L , C_L , and S_1 .

图 7-2. Propagation Delay



1. V_{CCI} is the supply pin associated with the input port.
2. V_{OH} and V_{OL} are typical output voltage levels that occur with specified R_L , C_L , and S_1 .

图 7-3. Input Transition Rise and Fall Rate



1. Output waveform on the condition that input is driven to a valid Logic Low.
2. Output waveform on the condition that input is driven to a valid Logic High.
3. V_{CCO} is the supply pin associated with the output port.
4. V_{OH} and V_{OL} are typical output voltage levels with specified R_L , C_L , and S_1 .

7-4. Enable Time And Disable Time

8 Detailed Description

8.1 Overview

The SN74LXCH1T45 is a 1-bit translating transceiver that uses two individually configurable power-supply rails. The device is operational with V_{CCA} and V_{CCB} supplies as low as 1.1 V and as high as 5.5 V. Additionally, the device operates with $V_{CCA} = V_{CCB}$. The A port is designed to track V_{CCA} , and the B port is designed to track V_{CCB} .

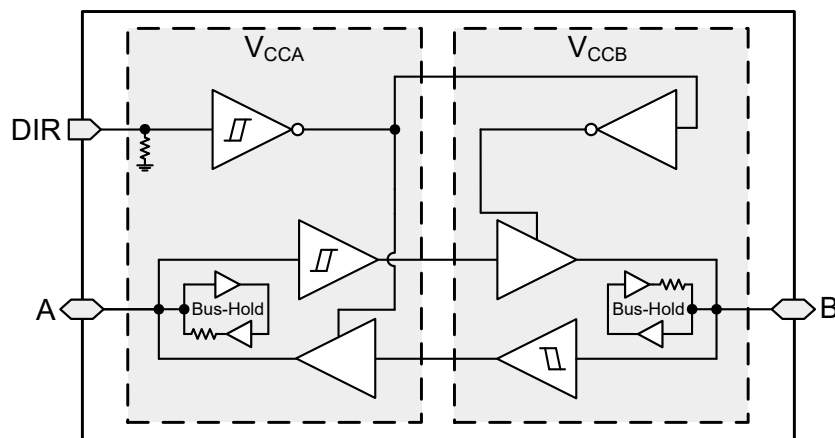
The SN74LXCH1T45 device is designed for asynchronous communication between data buses and transmits data from the A bus to the B bus or from the B bus to the A bus based on the logic level of the direction-control input (DIR). The control pin of the SN74LXCH1T45 (DIR) is referenced to V_{CCA} .

This device is fully specified for partial-power-down applications using the I_{off} current. The I_{off} protection circuitry ensures that no excessive current is drawn from or sourced into an input, output, or I/O while the device is powered down.

The V_{CC} isolation and V_{CC} disconnect feature ensures that if either V_{CC} is less than 100 mV or floating with the complementary supply within the recommended operating conditions, both I/O ports are set to the high-impedance state by disabling their outputs and the supply current is maintained.

Glitch-free power supply sequencing allows either supply rail to power on or off in any order while providing robust power sequencing performance.

8.2 Functional Block Diagram



Note: Bus-hold circuits are only present for data inputs, not control inputs

8.3 Feature Description

8.3.1 CMOS Schmitt-Trigger Inputs

Standard CMOS inputs are high impedance and are typically modeled as a resistor in parallel with the input capacitance given in the [Electrical Characteristics](#). The worst case resistance is calculated with the maximum input voltage, given in the [Absolute Maximum Ratings](#), and the maximum input leakage current, given in the [Electrical Characteristics](#), using ohm's law ($R = V \div I$).

The Schmitt-trigger input architecture provides hysteresis as defined by ΔV_T in the [Electrical Characteristics](#), which makes this device extremely tolerant to slow or noisy inputs. Driving the inputs slowly will increase dynamic current consumption of the device. See [Understanding Schmitt Triggers](#) for additional information regarding Schmitt-trigger inputs.

8.3.1.1 Control Inputs with Integrated Static Pull-Down Resistors

Similar to the data I/O's, floating control inputs can cause high current consumption. This device has integrated weak static pull-downs of 5-M Ω typical on the control inputs (DIR and OE) to help avoid this concern. These pull-downs are always present. For example, if the DIR pin is left floating, then the B port will be configured as an input and the A port will be configured as an output.

8.3.2 Balanced High-Drive CMOS Push-Pull Outputs

A balanced output allows the device to sink and source similar currents. The high drive capability of this device creates fast edges into light loads so routing and load conditions should be considered to prevent ringing. Additionally, the outputs of this device are capable of driving larger currents than the device can sustain without being damaged. The electrical and thermal limits defined in the [Absolute Maximum Ratings](#) must be followed at all times.

8.3.3 Partial Power Down (I_{off})

The inputs and outputs for this device enter a high-impedance state when the device is powered down, inhibiting current backflow into the device. I_{off} in the [Electrical Characteristics](#) specifies the maximum leakage into or out of any input or output pin on the device.

8.3.4 V_{CC} Isolation and V_{CC} Disconnect

The inputs and outputs for this device enter a high-impedance state when either supply is <100 mV, requiring one supply to connect to the device. Note: the bus-hold circuitry always remains active even when the device is disabled and all outputs are in the high-impedance state.

Either supply can be disconnected (floated), while the other supply is still connected and the device will maintain the maximum supply current specified by $I_{CCX(floating)}$ in the [Electrical Characteristics](#). The I/O's will not enter a high-impedance state unless the supply is disconnected after it is driven to <100 mV. $I_{off(float)}$ in the [Electrical Characteristics](#) specifies the maximum leakage into or out of any input or output pin on the device.

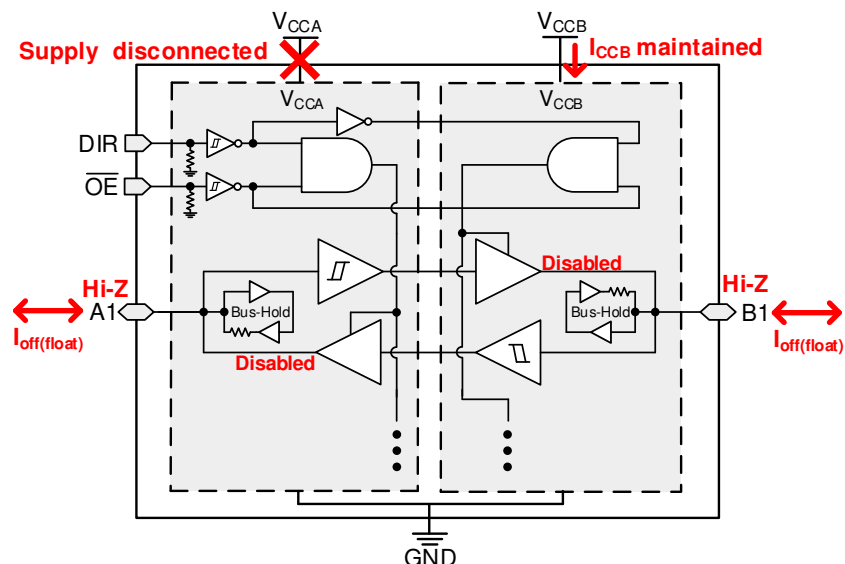


图 8-1. V_{CC} Disconnect Feature

8.3.5 Over-Voltage Tolerant Inputs

Input signals to this device can be driven above the supply voltage as long as they remain below the maximum input voltage value specified in the [Recommended Operating Conditions](#).

8.3.6 Glitch-Free Power Supply Sequencing

Either supply rail may be powered on or off in any order without producing a glitch on the I/Os (that is, where the output erroneously transitions to V_{CC} when it should be held low or vice versa). Glitches of this nature can be misinterpreted by a peripheral as a valid data bit, which could trigger a false device reset of the peripheral, a false device configuration of the peripheral, or even a false data initialization by the peripheral.

8.3.7 Negative Clamping Diodes

The inputs and outputs to this device have negative clamping diodes as depicted in [Figure 8-2](#).

CAUTION

Voltages beyond the values specified in [Section 6.1](#) table can cause damage to the device. The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

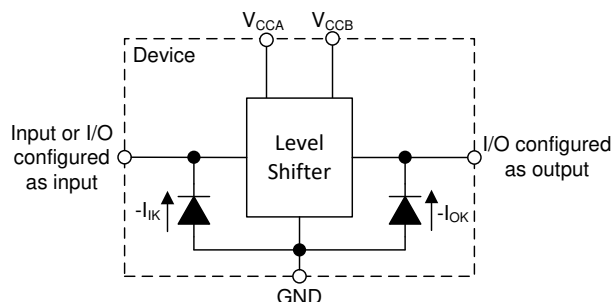


Figure 8-2. Electrical Placement of Clamping Diodes for Each Input and Output

8.3.8 Fully Configurable Dual-Rail Design

The V_{CCA} and V_{CCB} pins can be supplied at any voltage from 1.1 V to 5.5 V, making the device suitable for translating between any of the voltage nodes (1.2 V, 1.5 V, 1.8 V, 3.3 V, and 5.0 V).

8.3.9 Supports High-Speed Translation

The SN74LXCH1T45 device can support high data-rate applications. The translated signal data rate can be up to 420 Mbps when the signal is translated from 3.3 V to 5.0 V.

8.3.10 Bus-Hold Data Inputs

Each data input on this device includes a weak latch that maintains a valid logic level on the input. The state of these latches is unknown at startup and remains unknown until the input has been forced to a valid high or low state. After data is sent through a channel, the latch maintains the previous state on the input (if the line is left floating). It is not recommended to use pull-up or pull-down resistors together with a bus-hold input, as it may cause undefined inputs to occur which leads to excessive current consumption.

Bus-hold data inputs prevent floating inputs on this device. The [Implications of Slow or Floating CMOS Inputs](#) application report explains the problems associated with leaving the CMOS inputs floating. These latches remain active at all times, independent of all control signals such as direction control or output enable. The latches also remain active when the device is in the partial power down state, corresponding supply is still present, or when the I/O's are floated. The [Bus-Hold Circuit](#) application report has additional details regarding bus-hold inputs.

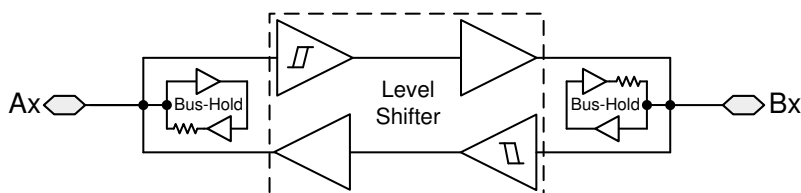


图 8-3. Schematic Description of Location of Bus-Hold Circuits

8.4 Device Functional Modes

表 8-1. Function Table⁽¹⁾

CONTROL INPUTS		PORT STATUS		OPERATION
OE	DIR	A PORT	B PORT	
L	L	Output (Enabled)	Input (Hi-Z)	B data to A bus
L	H	Input (Hi-Z)	Output (Enabled)	A data to B bus
H	X	Input (Hi-Z)	Input (Hi-Z)	Isolation

(1) Input circuits of the data I/Os are always active.

9 Application and Implementation

Note

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes, as well as validating and testing their design implementation to confirm system functionality.

9.1 Application Information

The SN74LXCH1T45 device can be used in level-translation applications for interfacing devices or systems operating at different interface voltages with one another. The SN74LXCH1T45 device is ideal for use in applications where a push-pull driver is connected to the data I/O. The maximum data rate can be up to 420 Mbps when the device translates a signal from 3.3 V to 5.0 V.

9.2 Enable Times

Calculate the enable times for the SN74LXCH1T45 using the following formulas:

$$t_{A_en} (\text{DIR to A}) = t_{dis} (\text{DIR to B}) + t_{pd} (\text{B to A}) \quad (1)$$

$$t_{B_en} (\text{DIR to B}) = t_{dis} (\text{DIR to A}) + t_{pd} (\text{A to B}) \quad (2)$$

In a bidirectional application, these enable times provide the maximum delay time from the time the DIR bit is switched until an output is expected. For example, if the SN74LXCH1T45 initially is transmitting from A to B, then the DIR bit is switched; the B port of the device must be disabled (t_{dis}) before presenting it with an input. After the B port has been disabled, an input signal applied to it appears on the corresponding A port after the specified propagation delay (t_{pd}). To avoid bus contention, care should be taken to not apply an input signal prior to the output being disabled (t_{dis} maximum).

9.3 Typical Application

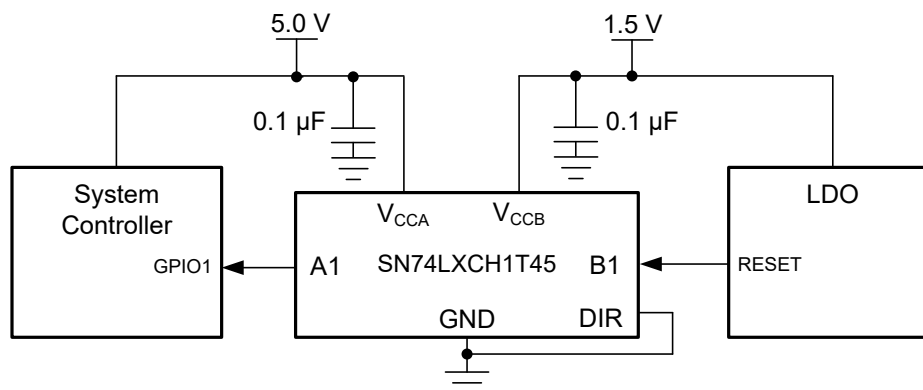


图 9-1. LED Driver Application

9.3.1 Design Requirements

Use the parameters listed in 表 9-1 for this design example.

表 9-1. Design Parameters

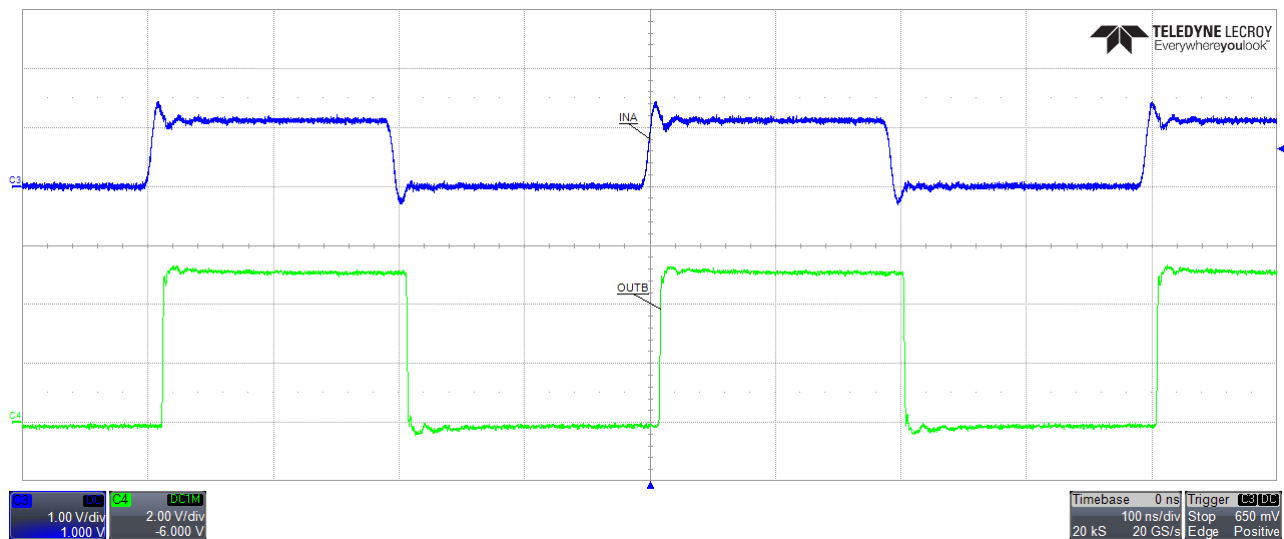
DESIGN PARAMETERS	EXAMPLE VALUES
Input voltage range	1.1 V to 5.5 V
Output voltage range	1.1 V to 5.5 V

9.3.2 Detailed Design Procedure

To begin the design process, determine the following:

- Input voltage range:
 - Use the supply voltage of the device that is driving the SN74LXCH1T45 device to determine the input voltage range. The value must exceed the high-level input voltage (V_{IH}) of the input port for a valid logic-high. The value must be less than the low-level input voltage (V_{IL}) of the input port for a valid logic low.
- Output voltage range:
 - Use the device's supply voltage that the SN74LXCH1T45 device is driving to determine the output voltage range.

9.3.3 Application Curve



9-2. Up Translation at 2.5 MHz (1.2 V to 5 V)

10 Power Supply Recommendations

Always apply a ground reference to the GND pins first. This device is designed for glitch free power sequencing without any supply sequencing requirements such as ramp order or ramp rate.

セクション 8.3.6 describes how this device was designed with various power supply sequencing methods in mind to help prevent unintended triggering of downstream devices.

11 Layout

11.1 Layout Guidelines

Following common printed-circuit board layout guidelines are recommended to ensure reliability of the device, which follows:

- Use bypass capacitors on the power supply pins and place them as close to the device as possible. A 0.1 μF capacitor is recommended, but transient performance can be improved by having both 1 μF and 0.1 μF capacitors in parallel as bypass capacitors.
- The high drive capability of this device creates fast edges into light loads; so routing and load conditions should be considered to prevent ringing.

11.2 Layout Example

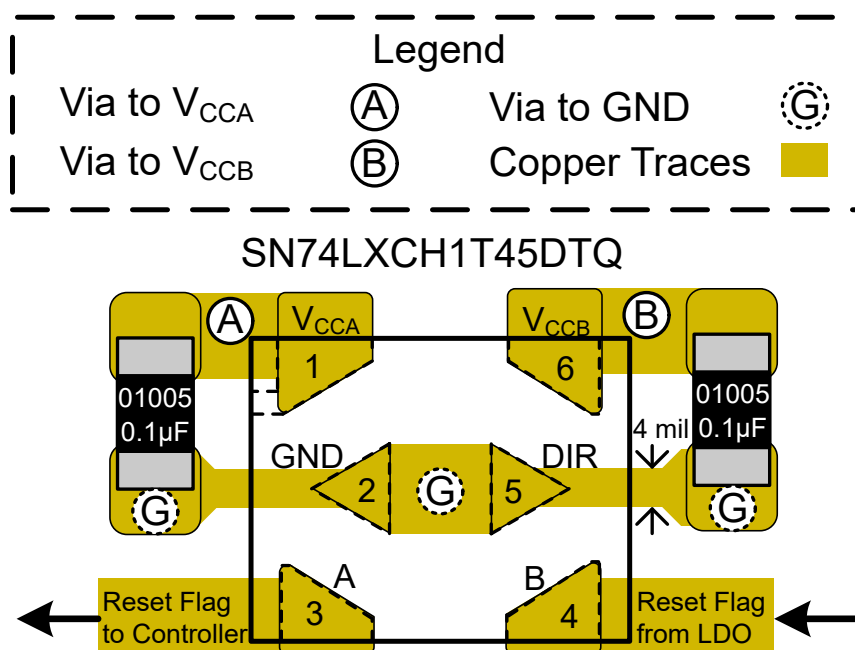


图 11-1. Layout Example

12 Device and Documentation Support

12.1 Documentation Support

12.1.1 Related Documentation

For related documentation, see the following:

- Texas Instruments, [CMOS Power Consumption and \$C_{pd}\$ Calculation](#) application report
- Texas Instruments, [Implications of Slow or Floating CMOS Inputs](#) application report
- Texas Instruments, [Semiconductor and IC Package Thermal Metrics](#) application report
- Texas Instruments, [System Considerations for Using Bus-Hold Circuits to Avoid Floating Inputs](#) application report

12.2 Receiving Notification of Documentation Updates

To receive notification of documentation updates, navigate to the device product folder on ti.com. Click on [Subscribe to updates](#) to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

12.3 サポート・リソース

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12.4 Trademarks

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12.5 Electrostatic Discharge Caution



This integrated circuit can be damaged by ESD. Texas Instruments recommends that all integrated circuits be handled with appropriate precautions. Failure to observe proper handling and installation procedures can cause damage.

ESD damage can range from subtle performance degradation to complete device failure. Precision integrated circuits may be more susceptible to damage because very small parametric changes could cause the device not to meet its published specifications.

12.6 Glossary

[TI Glossary](#) This glossary lists and explains terms, acronyms, and definitions.

13 Mechanical, Packaging, and Orderable Information

The following pages include mechanical, packaging, and orderable information. This information is the most current data available for the designated devices. This data is subject to change without notice and revision of this document. For browser-based versions of this data sheet, refer to the left-hand navigation.

PACKAGING INFORMATION

Orderable part number	Status (1)	Material type (2)	Package Pins	Package qty Carrier	RoHS (3)	Lead finish/ Ball material (4)	MSL rating/ Peak reflow (5)	Op temp (°C)	Part marking (6)
SN74LXCH1T45DCKR	Active	Production	SC70 (DCK) 6	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	2NNT
SN74LXCH1T45DCKR.A	Active	Production	SC70 (DCK) 6	3000 LARGE T&R	Yes	SN	Level-1-260C-UNLIM	-40 to 125	2NNT
SN74LXCH1T45DRYR	Active	Production	SON (DRY) 6	5000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	MJ
SN74LXCH1T45DRYR.A	Active	Production	SON (DRY) 6	5000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	MJ
SN74LXCH1T45DTQR	Active	Production	X2SON (DTQ) 6	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	MF
SN74LXCH1T45DTQR.A	Active	Production	X2SON (DTQ) 6	3000 LARGE T&R	Yes	NIPDAU	Level-1-260C-UNLIM	-40 to 125	MF

⁽¹⁾ **Status:** For more details on status, see our [product life cycle](#).

⁽²⁾ **Material type:** When designated, preproduction parts are prototypes/experimental devices, and are not yet approved or released for full production. Testing and final process, including without limitation quality assurance, reliability performance testing, and/or process qualification, may not yet be complete, and this item is subject to further changes or possible discontinuation. If available for ordering, purchases will be subject to an additional waiver at checkout, and are intended for early internal evaluation purposes only. These items are sold without warranties of any kind.

⁽³⁾ **RoHS values:** Yes, No, RoHS Exempt. See the [TI RoHS Statement](#) for additional information and value definition.

⁽⁴⁾ **Lead finish/Ball material:** Parts may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

⁽⁵⁾ **MSL rating/Peak reflow:** The moisture sensitivity level ratings and peak solder (reflow) temperatures. In the event that a part has multiple moisture sensitivity ratings, only the lowest level per JEDEC standards is shown. Refer to the shipping label for the actual reflow temperature that will be used to mount the part to the printed circuit board.

⁽⁶⁾ **Part marking:** There may be an additional marking, which relates to the logo, the lot trace code information, or the environmental category of the part.

Multiple part markings will be inside parentheses. Only one part marking contained in parentheses and separated by a "~" will appear on a part. If a line is indented then it is a continuation of the previous line and the two combined represent the entire part marking for that device.

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In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.

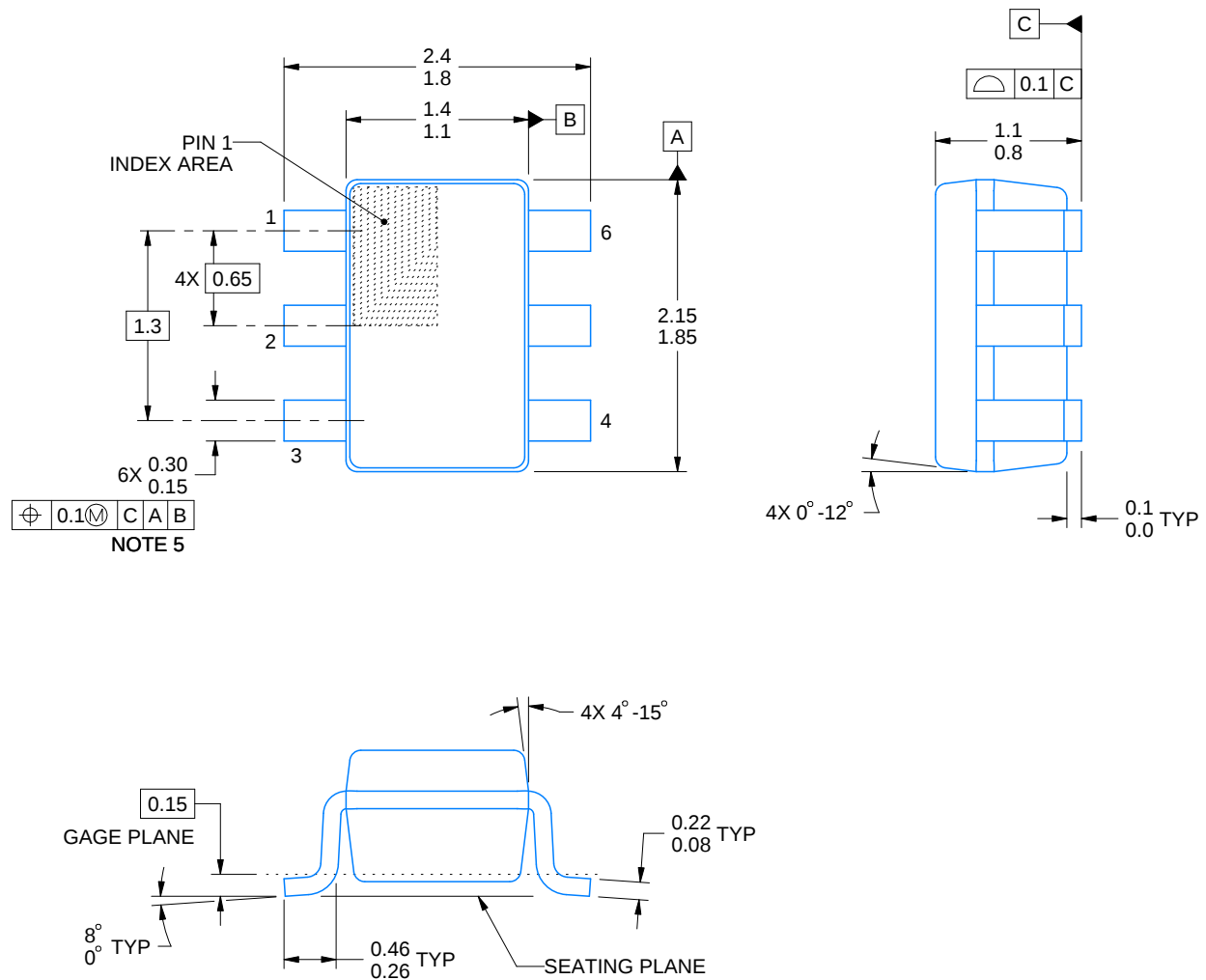
DCK0006A



PACKAGE OUTLINE

SOT - 1.1 max height

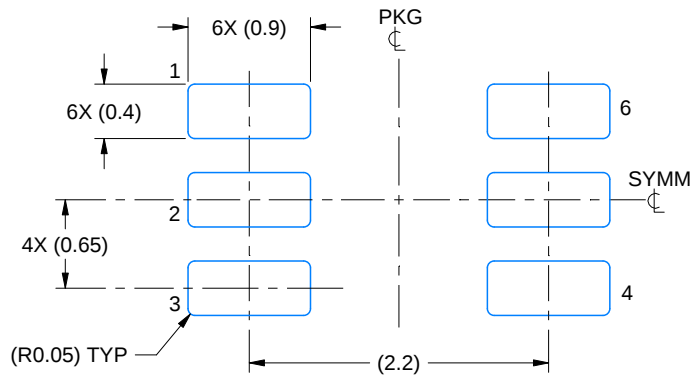
SMALL OUTLINE TRANSISTOR



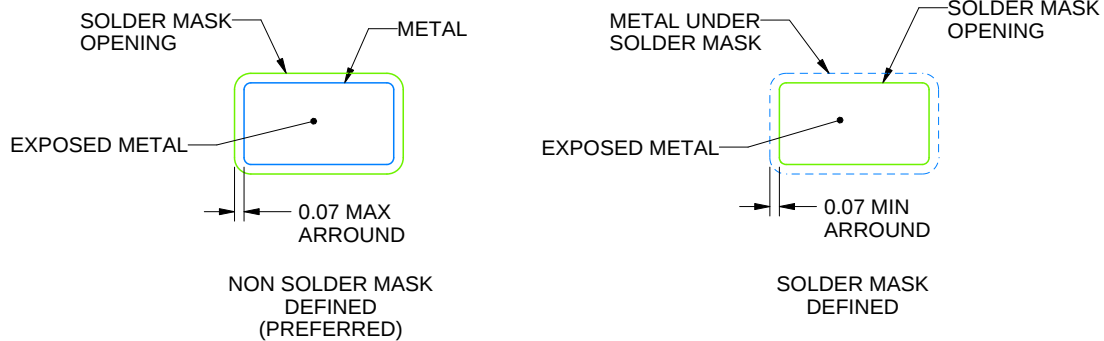
4214835/D 11/2024

NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
4. Falls within JEDEC MO-203 variation AB.



LAND PATTERN EXAMPLE
EXPOSED METAL SHOWN
SCALE:18X

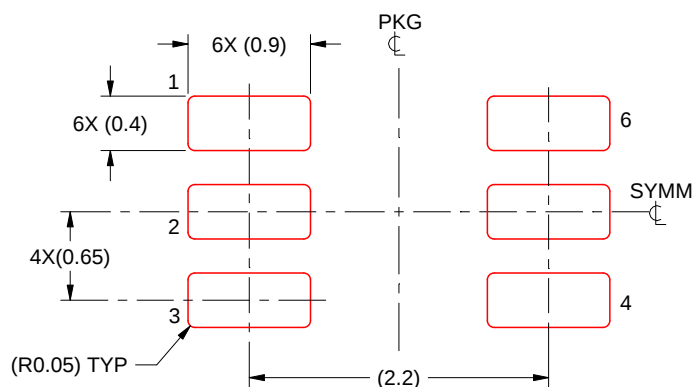


SOLDER MASK DETAILS

4214835/D 11/2024

NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.
6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SOLDER PASTE EXAMPLE
 BASED ON 0.125 THICK STENCIL
 SCALE:18X

4214835/D 11/2024

NOTES: (continued)

7. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
8. Board assembly site may have different recommendations for stencil design.

GENERIC PACKAGE VIEW

DRY 6

USON - 0.6 mm max height

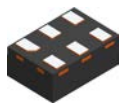
PLASTIC SMALL OUTLINE - NO LEAD



Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

4207181/G

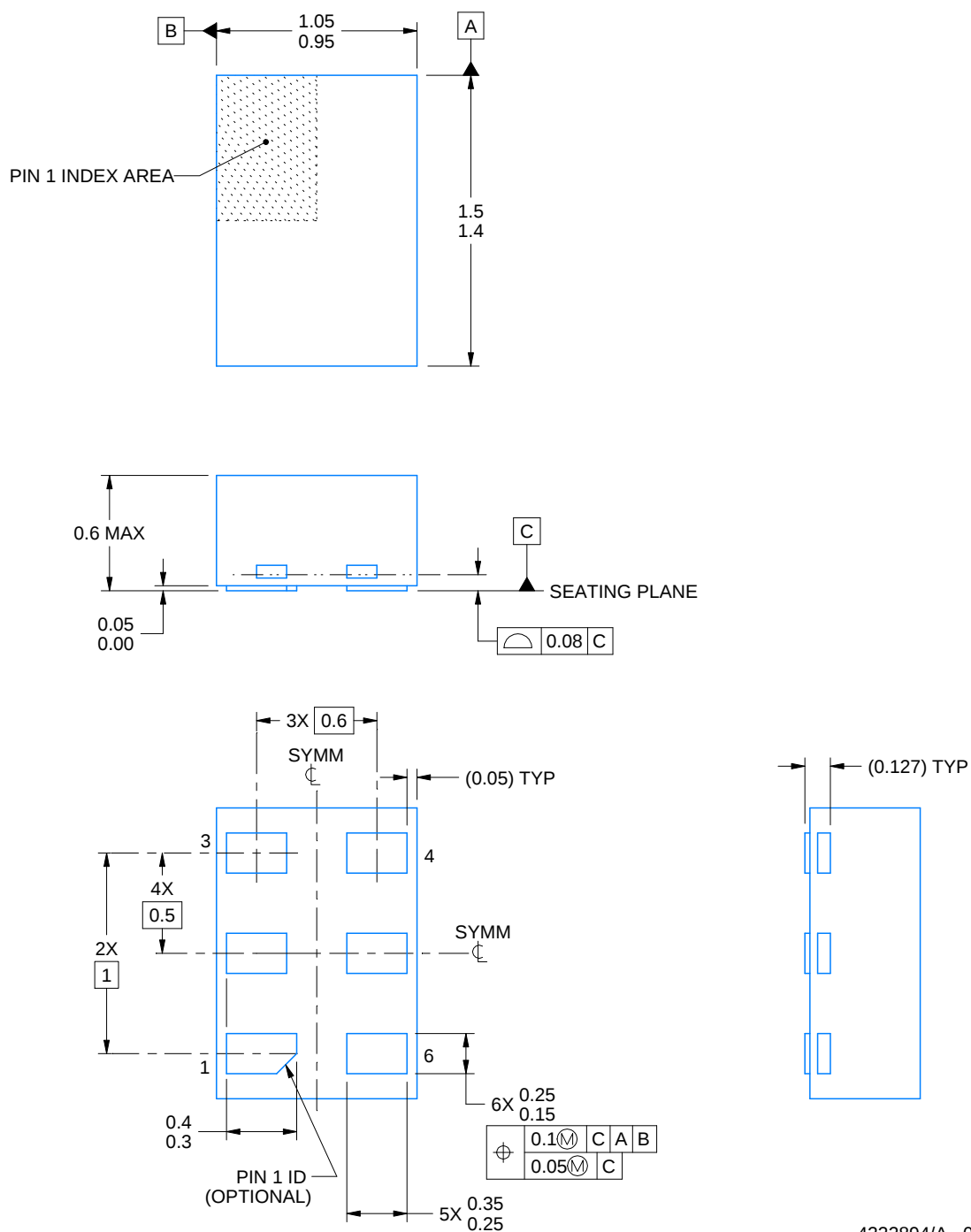
DRY0006A



PACKAGE OUTLINE

USON - 0.6 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



4222894/A 01/2018

NOTES:

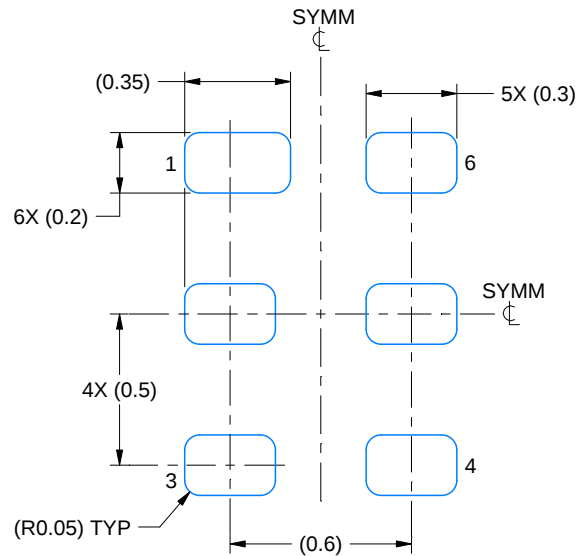
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.

EXAMPLE BOARD LAYOUT

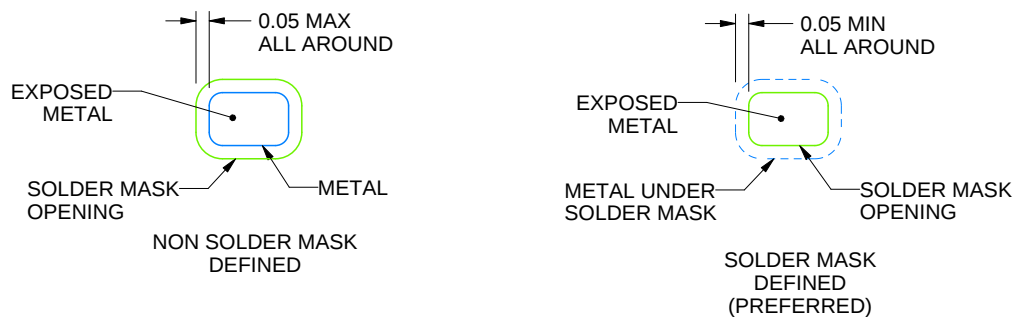
DRY0006A

USON - 0.6 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



LAND PATTERN EXAMPLE
1:1 RATIO WITH PKG SOLDER PADS
EXPOSED METAL SHOWN
SCALE:40X



SOLDER MASK DETAILS

4222894/A 01/2018

NOTES: (continued)

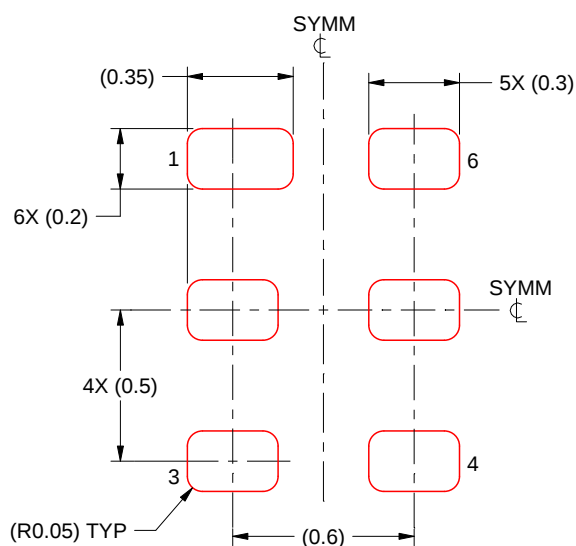
3. For more information, see QFN/SON PCB application report in literature No. SLUA271 (www.ti.com/lit/sluea271).

EXAMPLE STENCIL DESIGN

DRY0006A

USON - 0.6 mm max height

PLASTIC SMALL OUTLINE - NO LEAD

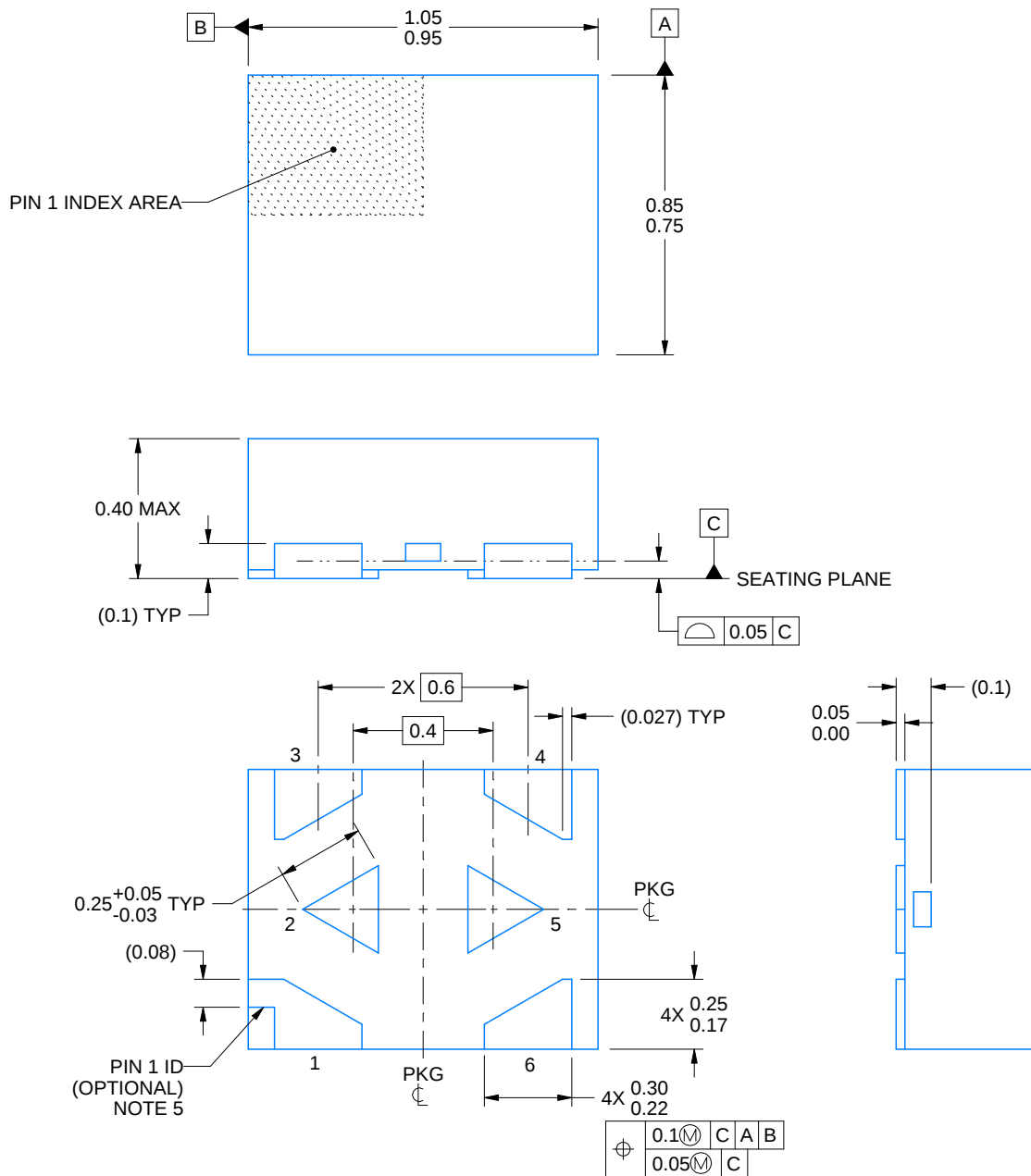


SOLDER PASTE EXAMPLE
BASED ON 0.075 - 0.1 mm THICK STENCIL
SCALE:40X

4222894/A 01/2018

NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



4224056/B 07/2024

NOTES:

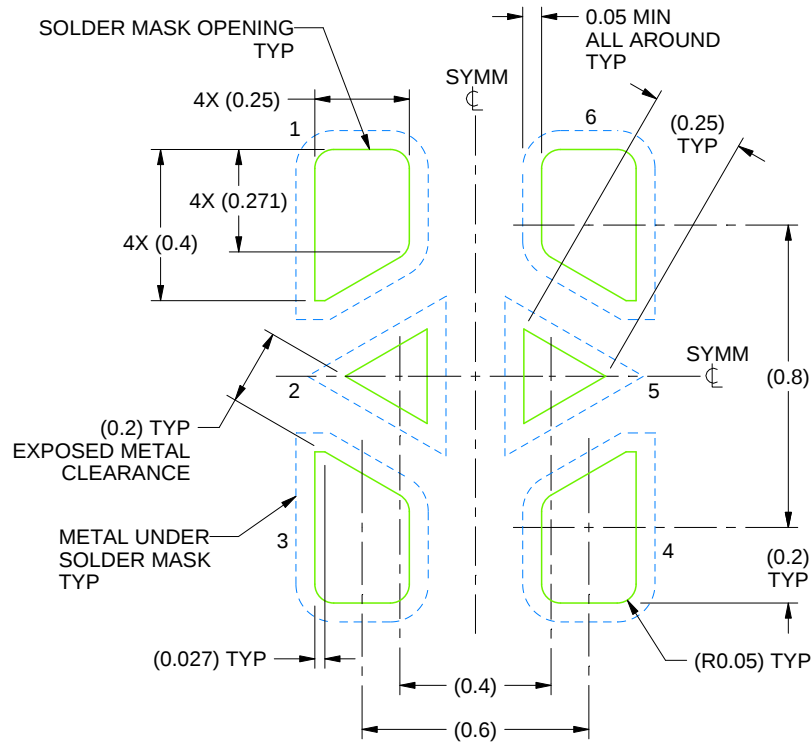
1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pads must be soldered to the printed circuit board for optimal thermal and mechanical performance.
4. The size and shape of this feature may vary.
5. Features may not exist. Recommend use of pin 1 marking on top of package for orientation purposes.

EXAMPLE BOARD LAYOUT

DTQ0006A

X2SON - 0.4 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



LAND PATTERN EXAMPLE
SOLDER MASK DEFINED
SCALE:50X

4224056/B 07/2024

NOTES: (continued)

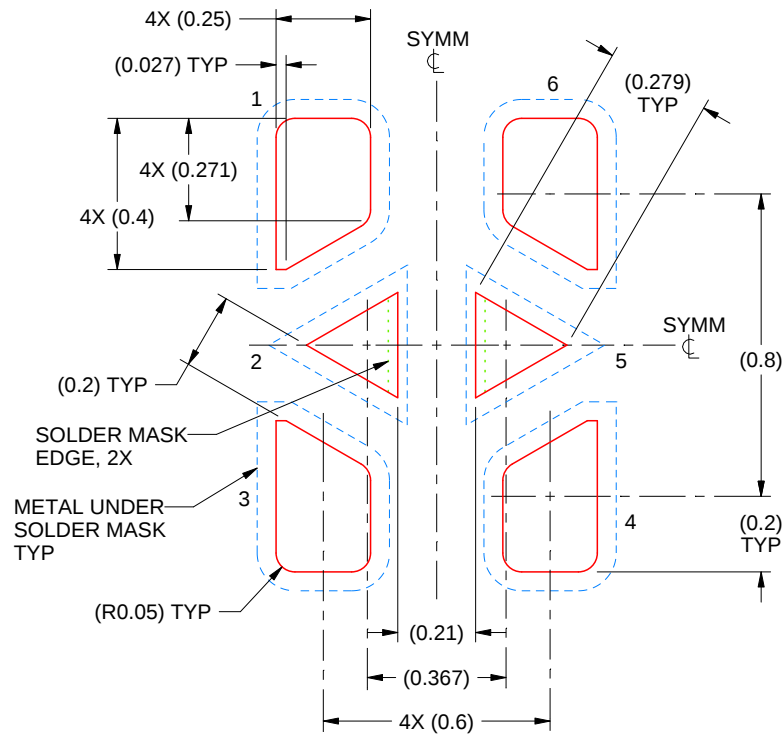
6. This package is designed to be soldered to a thermal pads on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/sluea271).
7. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.

EXAMPLE STENCIL DESIGN

DTQ0006A

X2SON - 0.4 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.07 mm THICK STENCIL

PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
SCALE:50X

4224056/B 07/2024

NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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